

Non-repetitive peak forward current

 $t < 1 \text{ s}$ I_{FSM} max. 600 mA

Storage temperature

 T_{stg} -50 to +150 °C

Junction temperature

 T_j max. 125 °C**THERMAL RESISTANCE**

From junction to ambient; mounted on a ceramic substrate of 10 mm × 8 mm × 0.6 mm

 $R_{th\ j-a}$ = 430 K/W**CHARACTERISTICS (per diode)** $T_{amb} = 25 \text{ °C}$ unless otherwise specified

Forward voltage

 $I_F = 0.1 \text{ mA}$ V_F max. 240 mV $I_F = 1 \text{ mA}$ V_F max. 320 mV $I_F = 10 \text{ mA}$ V_F max. 400 mV $I_F = 30 \text{ mA}$ V_F max. 500 mV

typ. 500 mV

 $I_F = 100 \text{ mA}$ V_F max. 1000 mV

Reverse current

 $V_R = 25 \text{ V}$ I_R < 2 μA

Reverse breakdown voltage

 $V_{(BR)R}$ > 30 V

Diode capacitance

 $V_R = 1 \text{ V}; f = 1 \text{ MHz}$ C_d < 15 pF

Reverse recovery time when switched from

 $I_F = 10 \text{ mA}$ to $I_R = 10 \text{ mA}$; $R_L = 100 \text{ }\Omega$;measured at $I_R = 1 \text{ mA}$ t_{rr} < 5 ns

SCHOTTKY BARRIER DIODES

BAT54A dual diodes, common anode

BAT54C dual diodes, common cathode and

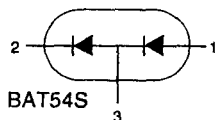
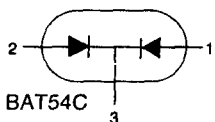
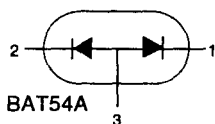
BAT54S dual diodes, in series

Marking

BAT54A - 42

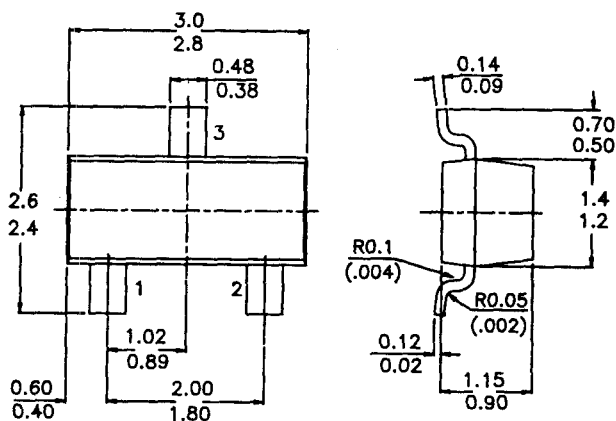
BAT54C - 43

BAT54S - 44



PACKAGE OUTLINE DETAILS

ALL DIMENSIONS IN mm



ABSOLUTE MAXIMUM RATINGS (per diode)

Continuous reverse voltage

$$V_R \quad \text{max.} \quad 30 \text{ V}$$

Forward current (DC)

 I_F max. 200 mA

Forward voltage at $I_F = 10 \text{ mA}$

$$V_F < 400 \text{ mV}$$

Reverse recovery time when switched from

$$I_F = 10 \text{ mA to } I_R = 10 \text{ mA}; R_L = 100 \Omega;$$

measured at $I_R = 1 \text{ mA}$

$$t_{rr} < 5 \text{ ns}$$

Junction temperature

T _i	max.	125 °C
----------------	------	--------

RATINGS (per diode) (at $T_A = 25^\circ\text{C}$ unless otherwise specified)

Limiting values

Repetitive peak reverse voltage

V _{RRM}	max.	30 V
------------------	------	------

Forward current (DC)

I_F max. 200 mA

Repetitive peak forward current

I_{FRM}	max.	300 mA
------------------	------	--------